

ABSTRACT OF THE DISCLOSURE

An apparatus and method to provide a via with an increased via contact area. A semiconductor support layer is coupled to a dielectric layer and a contact is coupled to the dielectric layer. A via, having an enlarged end within the 5 semiconductor support layer, passes through the semiconductor support layer and the dielectric layer and connects to the contact. In one embodiment, the formation of the via and the enlarged end in the semiconductor support layer are completed in a single dry etch process.